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(54) Title: SANDWICH PACKAGE FOR MICROELECTRONICS

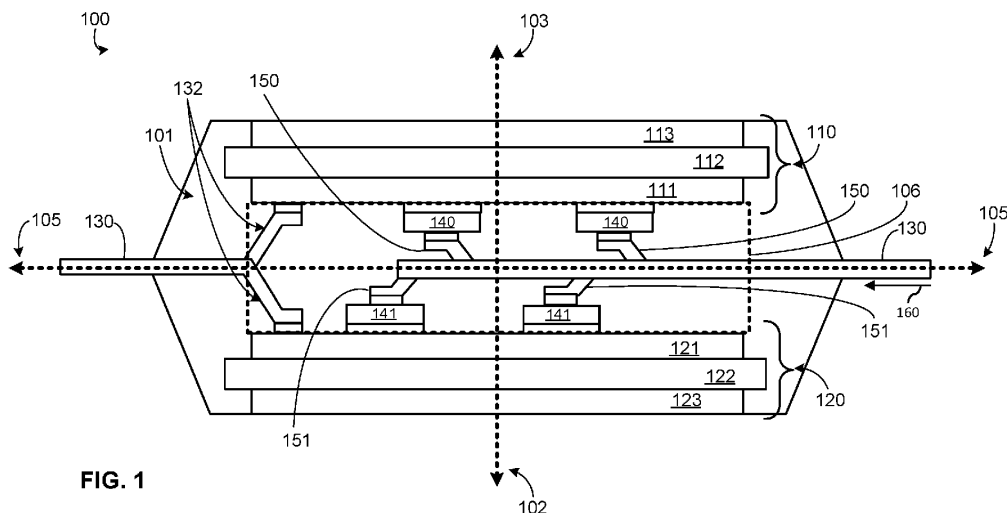


FIG. 1

(57) Abstract: A transistor configured for higher power can be constructed using multiple transistor dies coupled in parallel. This approach of distributing power and heat over multiple transistor dies can allow each transistor die to be made smaller, which can be helpful in improving yield. This is especially true for emerging technologies, such as silicon carbide (SiC). Power modules for power conversion may require a plurality of these multi-die transistors in a package. A package that accommodates the numerous connections required for a multi-die power module is disclosed. The package utilizes a lead frame to provide a three-dimensional sandwich structure in which multiple dies are positioned between two direct bonded copper (DBC) substrates.

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